

2ST2121

High power PNP epitaxial planar bipolar transistor

Features

- High breakdown voltage V_{CEO} = -250 V
- Complementary to 2ST5949
- Typical f_t = 25 MHz
- Fully characterized at 125 °C

Applications

Audio power amplifier

Description

The device is a PNP transistor manufactured using new BiT-LA (Bipolar transistor for linear amplifier) technology. The resulting transistor shows good gain linearity behaviour.

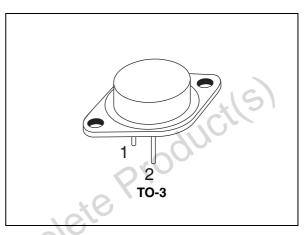


Figure 1. Internal schematic diagram

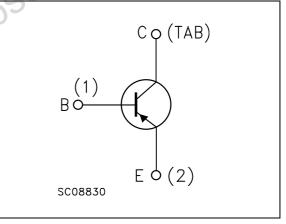


Table 1. Device summary

Order code	Marking	Package	Packaging
2ST2121	2ST2121	TO-3	tray

Absolute maximun rating 1

Table 2. Absolute maximum rating

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-base voltage (I _E = 0)	-250	V
V _{CEO}	Collector-emitter voltage $(I_B = 0)$	-250	V
V _{EBO}	Emitter-base voltage ($I_C = 0$)	-6	V
I _C Collector current		-17	Α
I _{CM}	Collector peak current (t _P < 5 ms)	-34	Α
P _{TOT}	Total dissipation at $T_c = 25 \text{ °C}$	250	W
T _{stg}	Storage temperature	-65 to 200	⊃ °C
Τ _J	Max. operating junction temperature	200	°C
Table 3.	Thermal data	rodv.	

Table 3. Thermal data

Symb	Parameter		Value	Unit
R _{thj-ca}	se Thermal resistance junction-case	max	0.7	°C/W
	Auct(S) Obs	30182		

2 Electrical characteristics

(T_{case} = 25 °C; unless otherwise specified)

Table 4.	Electrical	characteristics
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Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
I _{CBO}	Collector cut-off current (I _E = 0)	V _{CB} = -250 V			-5	μA
I _{EBO}	Emitter cut-off current $(I_{\rm C} = 0)$	V _{EB} = -6 V			-5	μA
V _{(BR)CEO} ⁽¹⁾	Collector-emitter breakdown voltage ($I_B = 0$)	I _C = -50 mA	-250		29	V
V _{(BR)CBO}	Collector-base breakdown voltage (I _E = 0)	I _C = -100 μΑ	-250	5		V
V _{(BR)EBO} ⁽¹⁾	Emitter-base breakdown voltage (I _C = 0)	I _E = -1 mA	-6			V
V _{CE(sat)} ⁽¹⁾	Collector-emitter saturation voltage	I _C = -8 A I _B = -800 mA			-3	V
V _{BE} ⁽¹⁾	Base-emitter voltage	I _C = -7 A V _{CE} = -5 V			-1.5	V
h _{FE}	IDC current dain	$I_{C} = -1 A$ $V_{CE} = -5 V$ $I_{C} = -7 A$ $V_{CE} = -5 V$	80 35		160	
f _T	Transition frequency	I _C = -1 A V _{CE} = -5 V		25		MHz

1. Pulsed duration = 300 μs, duty cycle ≤ 1.5%

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Electrical characteristics (curves) 2.1

-1

-10

I_c (A)

-0.1

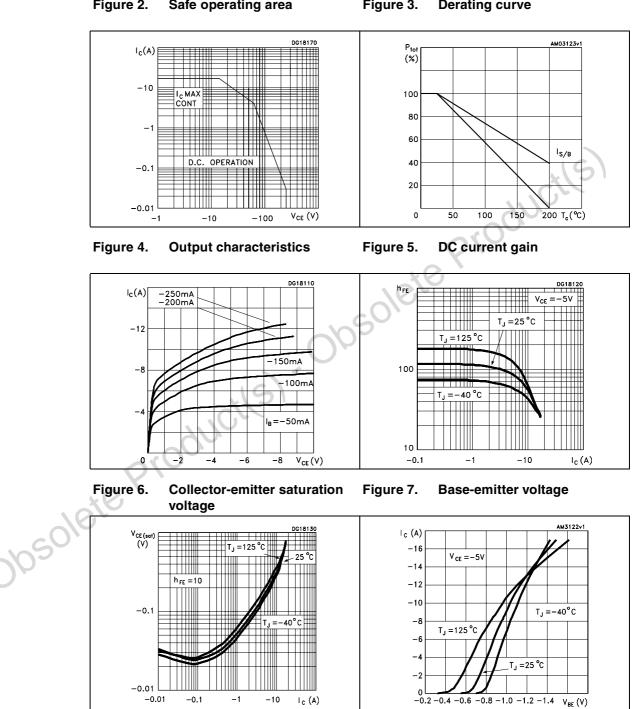


Figure 2. Safe operating area

Figure 3. **Derating curve**

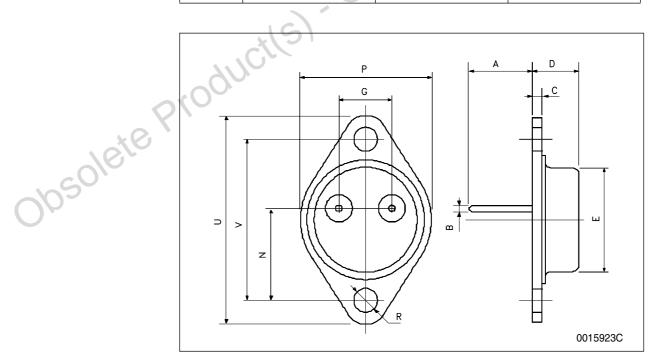
3 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com

obsolete Product(s). Obsolete Product(s)

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TO-3 mechanical data					
DIM.					
Diwi.	min.	typ	max.		
A	11.00		13.10		
В	0.97		1.15		
С	1.50		1.65		
D	8.32		8.92		
E	19.00		20.00		
G	10.70	0	11.10		
N	16.50		17.20		
Р	25.00	10,10	26.00		
R	4.00	~010	4.09		
U	38.50	3	39.30		
V	30.00		30.30		



4 Revision history

Table 5. Document revision history

	Date	Revision	Changes
	11-Oct-2007	1	Initial release.
	09-Dec-2007 2 Datasheet status changed from target specification to predata.		Datasheet status changed from target specification to preliminary data.
	16-May-2008	3	Added new graphics.
	11-Jul-2008	4	Updated maximum operating junction temperature value.
	13-Nov-2008	5	Document status promoted from preliminary data to datasheet.
			obsolete Production



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